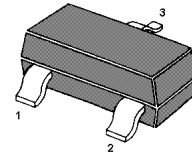
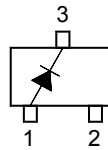


MMBD4448

Silicon Epitaxial Planar Switching Diode

Features

- Fast switching speed
- High Conductance



Marking Code: **5D**
TO-236 Plastic Package

Applications

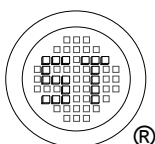
- For general purpose switching

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|---|----------------|---------------|------------------|
| Peak Reverse Voltage | V_{RM} | 100 | V |
| Reverse Voltage | V_R | 75 | V |
| Average Rectified Forward Current | $I_{F(AV)}$ | 250 | mA |
| Forward Continuous Current | I_{FM} | 500 | mA |
| Non-repetitive Peak Forward Surge Current | I_{FSM} | 2 | A |
| | | 4 | |
| Power Dissipation | P_d | 350 | mW |
| Junction and Storage Temperature Range | T_j, T_{stg} | - 65 to + 150 | $^\circ\text{C}$ |

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

| Parameter | Symbol | Min. | Max. | Unit |
|---|----------|------|-------|---------------|
| Forward Voltage at $I_F = 5\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 100\text{ mA}$ at $I_F = 150\text{ mA}$ | V_F | 0.62 | 0.72 | V |
| | | - | 0.855 | |
| | | - | 1 | |
| | | - | 1.25 | |
| Reverse Current at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 25\text{ V}, T_j = 150\text{ }^\circ\text{C}$ at $V_R = 75\text{ V}, T_j = 150\text{ }^\circ\text{C}$ | I_R | - | 25 | nA |
| | | - | 2.5 | μA |
| | | - | 30 | μA |
| | | - | 50 | μA |
| Junction Capacitance at $V_R = 0\text{ V}, f = 1\text{ MHz}$ | C_j | - | 4 | pF |
| Reverse Recovery Time at $I_F = I_R = 10\text{ mA}, I_{rr} = 0.1 \times I_R, R_L = 100\ \Omega$ | t_{rr} | - | 4 | ns |



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Dated : 16/03/2015 Rev:01

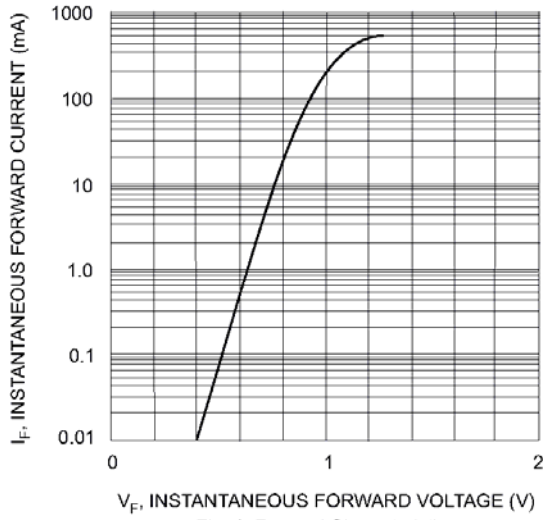


Fig. 1 Forward Characteristics

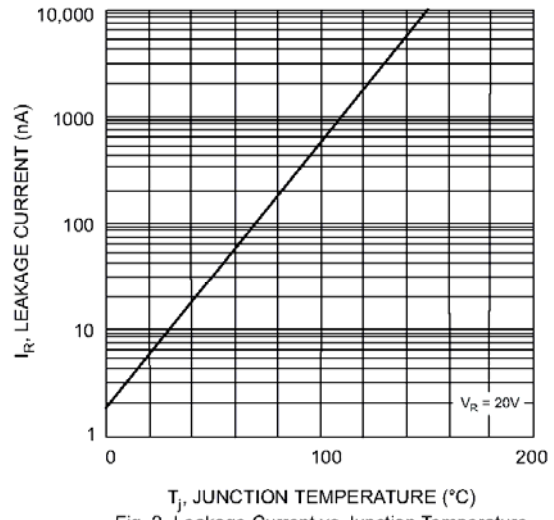
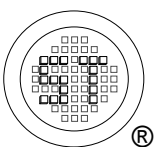


Fig. 2 Leakage Current vs Junction Temperature



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